PROCESS CPD75

Schottky Rectifier

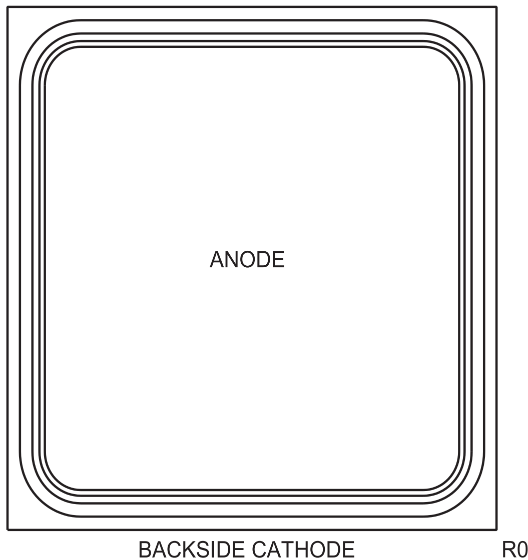
5 Amp Schottky Barrier Rectifier Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Die Size	72.5 x 72.5 MILS
Die Thickness	11.8 MILS
Anode Bonding Pad Area	63.8 x 63.8 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER
2,160

PRINCIPAL DEVICE TYPES
CZSH5-40
CZSH10-40C (Dual Chip)

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

www.centralsemi.com/chip

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